## MJD47, MJD50

## High Voltage Power <br> Transistors

DPAK For Surface Mount Applications
Designed for line operated audio output amplifier, SWITCHMODE ${ }^{T M}$ power supply drivers and other switching applications.

## Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- 250 and 400 V (Min) - $\mathrm{V}_{\mathrm{CEO}}$ (sus)
- 1 A Rated Collector Current
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V

Machine Model, C > 400 V

- Pb -Free Packages are Available

MAXIMUM RATINGS

| Rating |  |  | Symbol | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Voltage |  | MJD47 <br> MJD50 | $\mathrm{V}_{\text {CEO }}$ | $\begin{aligned} & 250 \\ & 400 \end{aligned}$ | Vdc |
| Collector-Base Voltage |  | MJD47 <br> MJD50 | $\mathrm{V}_{C B}$ | $\begin{aligned} & 350 \\ & 500 \end{aligned}$ | Vdc |
| Emitter-Base Voltage |  |  | $\mathrm{V}_{\mathrm{EB}}$ | 5 | Vdc |
| Collector Current - Continuous <br> - Peak |  |  | $I_{C}$ | 1 | Adc |
| Base Current |  |  | $\mathrm{I}_{\mathrm{B}}$ | 0.6 | mAdc |
| Total Power Dissipation @ $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ Derate above $25^{\circ} \mathrm{C}$ |  |  | $\mathrm{P}_{\mathrm{D}}$ | $\begin{gathered} 15 \\ 0.12 \end{gathered}$ | $\begin{gathered} \mathrm{W} \\ \mathrm{~W} /{ }^{\circ} \mathrm{C} \end{gathered}$ |
| Total Power Dissipation (Note 1) <br> @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ |  |  | $\mathrm{P}_{\mathrm{D}}$ | $\begin{gathered} 1.56 \\ 0.0125 \end{gathered}$ | $\begin{gathered} \mathrm{W} \\ \mathrm{~W} /{ }^{\circ} \mathrm{C} \end{gathered}$ |
| Operating and Storage Junction Temperature Range |  |  | $\mathrm{T}_{\mathrm{J},} \mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Thermal Resistance Junction-to-Case | $\mathrm{R}_{\theta \mathrm{JC}}$ | 8.33 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal <br> (Note 1) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 80 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Temperature for Soldering Purpose Junction-to-Ambient | $\mathrm{T}_{\mathrm{L}}$ | 260 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ON Semiconductor ${ }^{\circledR}$
http://onsemi.com

NPN SILICON POWER
TRANSISTORS
1 AMPERE
250, 400 VOLTS, 15 WATTS


DPAK CASE 369C STYLE 1

MARKING DIAGRAM


Y = Year
WW = Work Week
Jxx = Device Code $x x=47$ or 50
$\mathrm{G}=\mathrm{Pb}-$ Free Package

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## MJD47, MJD50

ELECTRICAL CHARACTERISTICS $\left(T_{C}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| Collector-Emitter Sustaining Voltage (Note 2) $\left(I_{C}=30 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ | $\begin{aligned} & \text { MJD47 } \\ & \text { MJD50 } \end{aligned}$ | $\mathrm{V}_{\text {CEO(sus) }}$ | $\begin{aligned} & 250 \\ & 400 \end{aligned}$ | - | Vdc |
| $\begin{aligned} & \text { Collector Cutoff Current } \\ & \left(\mathrm{V}_{\mathrm{CE}}=150 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0\right) \\ & \left(\mathrm{V}_{\mathrm{CE}}=300 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0\right) \end{aligned}$ | $\begin{aligned} & \text { MJD47 } \\ & \text { MJD50 } \end{aligned}$ | ICEO | - | $\begin{aligned} & 0.2 \\ & 0.2 \end{aligned}$ | mAdc |
| $\begin{aligned} & \text { Collector Cutoff Current } \\ & \left(V_{C E}=350 \mathrm{Vdc}, \mathrm{~V}_{\mathrm{BE}}=0\right) \\ & \left(\mathrm{V}_{\mathrm{CE}}=500 \mathrm{Vdc}, \mathrm{~V}_{\mathrm{BE}}=0\right) \end{aligned}$ | $\begin{aligned} & \text { MJD47 } \\ & \text { MJD50 } \end{aligned}$ | $I_{\text {CES }}$ | - | $\begin{aligned} & 0.1 \\ & 0.1 \end{aligned}$ | mAdc |
| Emitter Cutoff Current $\left(\mathrm{V}_{\mathrm{BE}}=5 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0\right)$ |  | $\mathrm{I}_{\text {ebo }}$ | - | 1 | mAdc |

ON CHARACTERISTICS (Note 2)

| $\begin{aligned} & \text { DC Current Gain } \\ & \quad\left(I_{C}=0.3 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{Vdc}\right) \\ & \quad\left(\mathrm{I}_{\mathrm{C}}=1 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{Vdc}\right) \end{aligned}$ | $\mathrm{h}_{\text {FE }}$ | $\begin{aligned} & 30 \\ & 10 \end{aligned}$ | 150 - | - |
| :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Saturation Voltage $\left(I_{C}=1 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=0.2 \mathrm{Adc}\right)$ | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | - | 1 | Vdc |
| Base-Emitter On Voltage $\left(\mathrm{lC}=1 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{Vdc}\right)$ | $\mathrm{V}_{\mathrm{BE} \text { (on) }}$ | - | 1.5 | Vdc |

## DYNAMIC CHARACTERISTICS

| Current Gain — Bandwidth Product <br> $\left(\mathrm{I}_{\mathrm{C}}=0.2\right.$ Adc, $\left.\mathrm{V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}=2 \mathrm{MHz}\right)$ | $\mathrm{f}_{\mathrm{T}}$ | 10 | - |
| :--- | :---: | :---: | :---: |
| Small-Signal Current Gain <br> $\left(\mathrm{I}_{\mathrm{C}}=0.2\right.$ Adc, $\left.\mathrm{V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}=1 \mathrm{kHz}\right)$ | $\mathrm{h}_{\mathrm{fe}}$ | 25 | - |

2. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, Duty Cycle $\leq 2 \%$.

## TYPICAL CHARACTERISTICS



Figure 1. Power Derating


Figure 2. Switching Time Equivalent Circuit

## MJD47, MJD50



Figure 3. DC Current Gain


Figure 4. "On" Voltages


Figure 5. Thermal Response


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{C}-V_{C E}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}=150^{\circ} \mathrm{C} ; \mathrm{T}_{\mathrm{C}}$ is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to $10 \%$ provided $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}$ $\leq 150^{\circ} \mathrm{C}$. $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

## MJD47, MJD50



Figure 7. Turn-On Time


Figure 8. Turn-Off Time

ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :---: | :---: | :---: |
| MJD47 | 369C |  |
| MJD47G | $\begin{gathered} 369 \mathrm{C} \\ \text { (Pb-Free) } \end{gathered}$ | 75 Units / Rail |
| MJD47T4 | 369C |  |
| MJD47T4G | $\begin{gathered} 369 \mathrm{C} \\ \text { (Pb-Free) } \end{gathered}$ | 2500 / Tape \& Reel |
| MJD50 | 369C |  |
| MJD50G | $\begin{gathered} 369 \mathrm{C} \\ \text { (Pb-Free) } \end{gathered}$ | 75 Units / Rail |
| MJD50T4 | 369C |  |
| MJD50T4G | $\begin{gathered} 369 \mathrm{C} \\ \text { (Pb-Free) } \end{gathered}$ | 2500 / Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MJD47, MJD50

## PACKAGE DIMENSIONS

DPAK
CASE 369C-01
ISSUE D

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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